-142' 120, 160 141 120 110 ۵, 120, FIG. 1 (PRIOR ART) 160 141 120 170 110 142 150 142 /114 | 120'40 116 118 142-120-100 -391/1

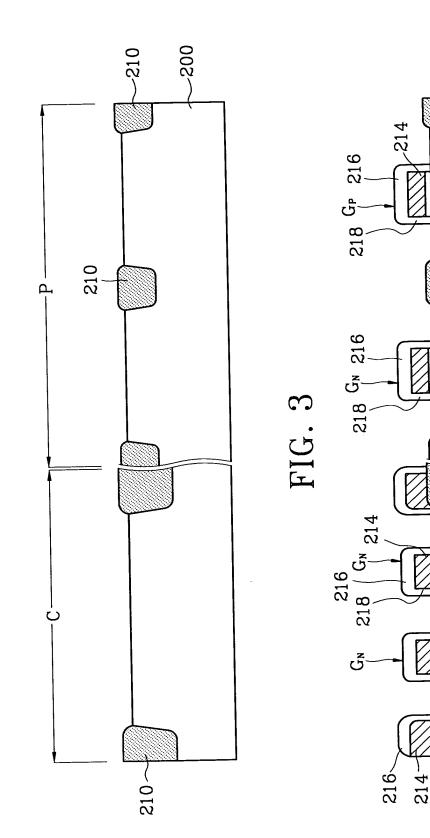
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FIG. 2



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(212 > 220

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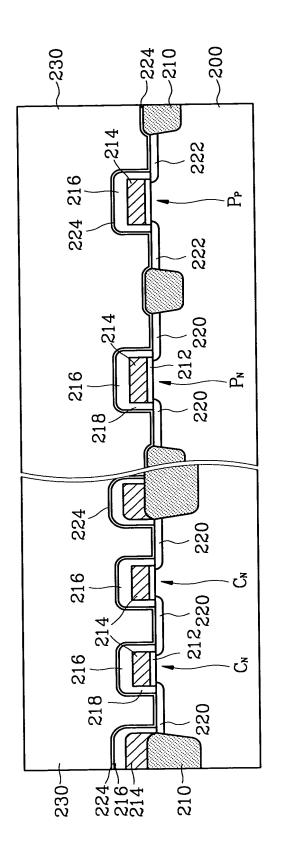
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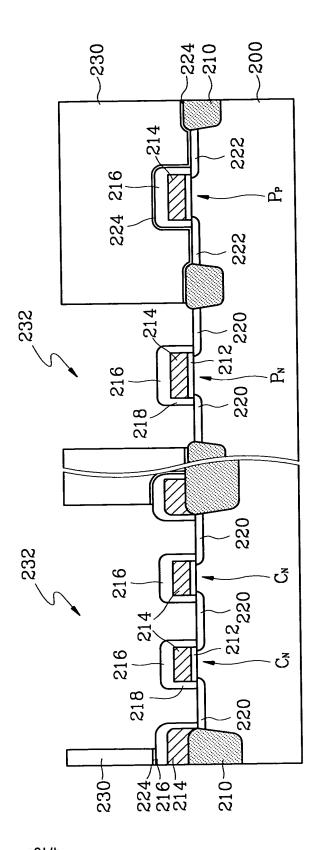
2/16.9

FIG. 4



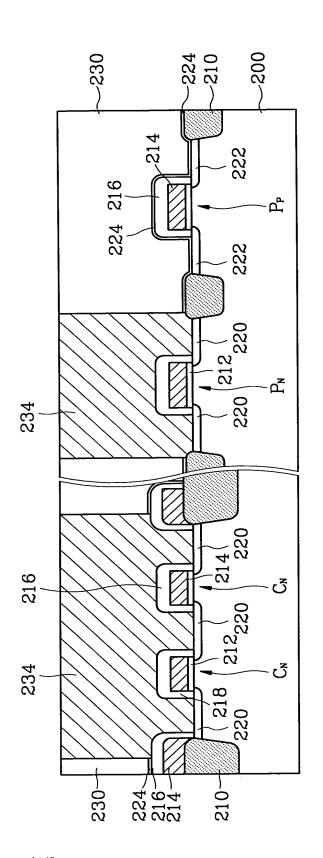
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FIG. 5



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FIG. 6



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WETHOD OF FORMING SEMICONDUCTOR DEVICE HAVING CONTACT PAD ON SOURCE/DRAIN REGION IN PERIPHERAL CIRCUIT

AREA

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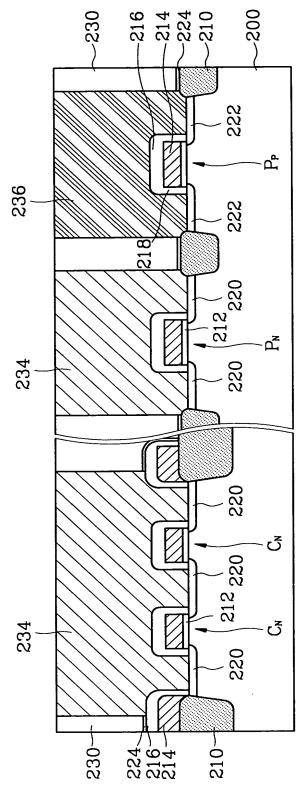
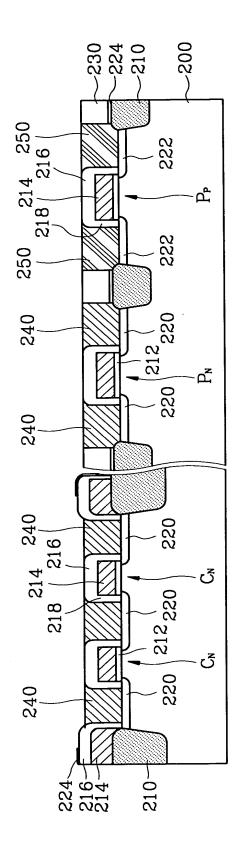


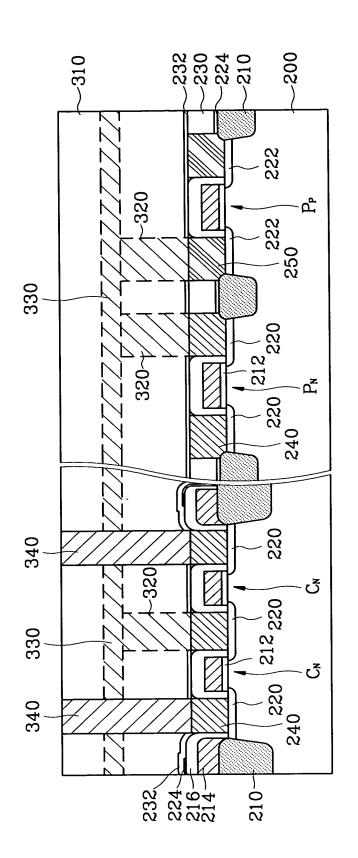
FIG. 8



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FIG. 9



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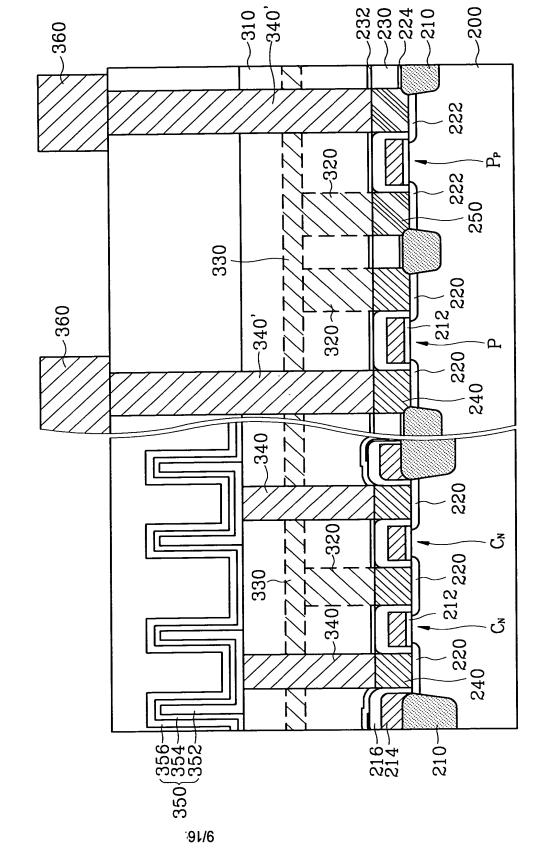
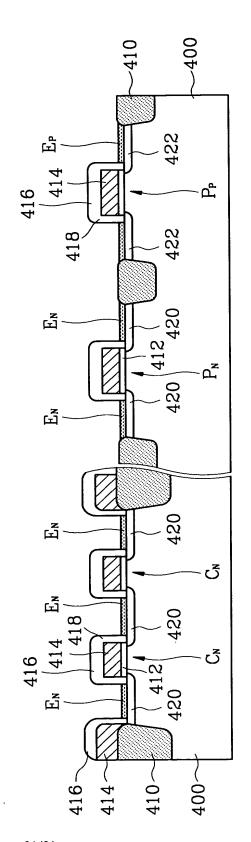


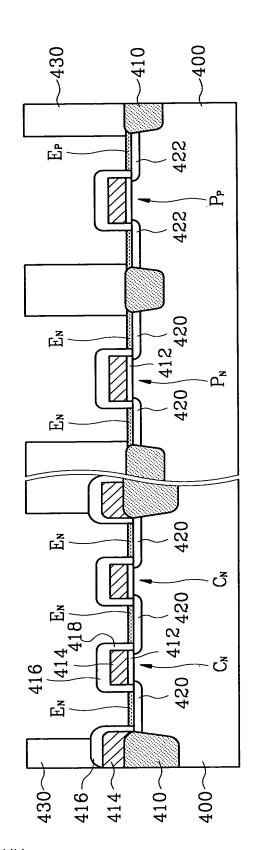
FIG.

FIG. 11



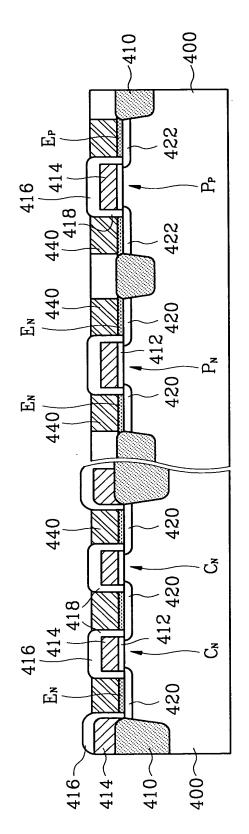
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FIG. 12



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FIG. 13



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FIG. 14A

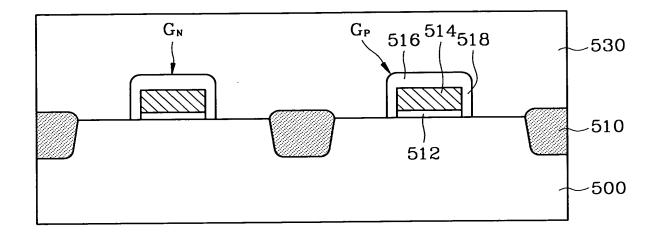
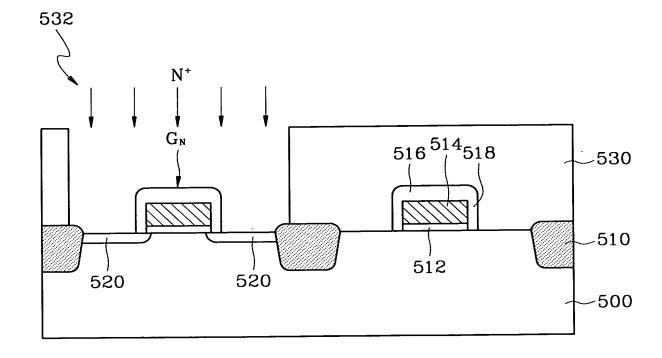


FIG. 14B



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FIG. 14C

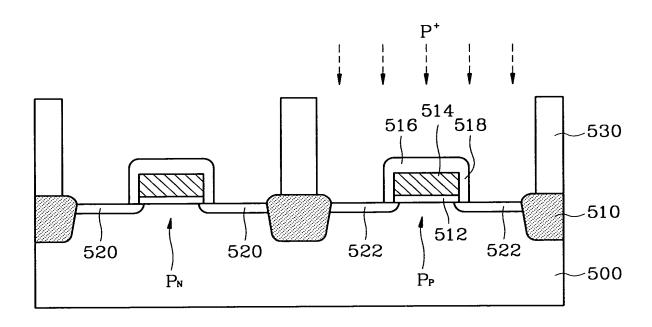
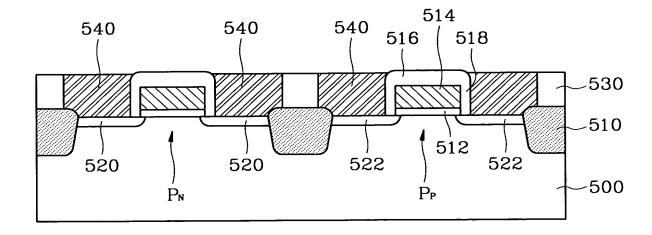


FIG. 14D



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FIG. 15A

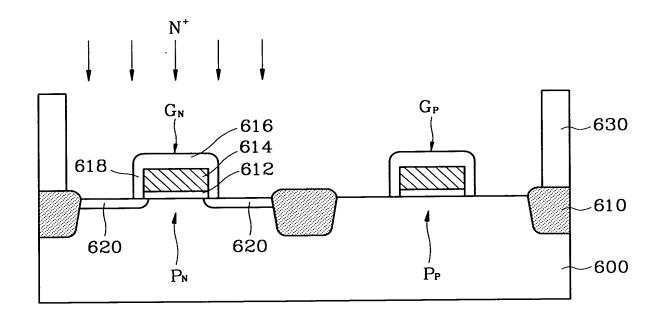
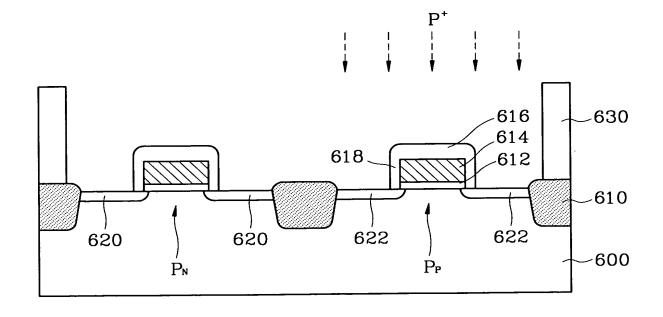


FIG. 15B



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FIG. 15C

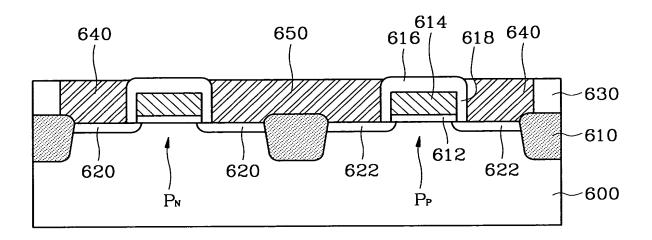


FIG. 16 (PRIOR ART)

